

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

**PATENT**

In re application of:

Calvez et al.

) Group Art Unit: Unknown  
)

Serial No. 10/550,846

) Examiner: N/A  
)

Filed: March 24, 2004 (I.A.)

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)  
For: IMPROVEMENTS IN AND  
RELATING TO VERTICAL-  
CAVITY SEMICONDUCTOR  
OPTICAL DEVICES  
)

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Janet McGee

Commissioner for Patents  
P.O. Box 1450  
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INFORMATION DISCLOSURE STATEMENT

Dear Sir:

Applicant wishes to call to the attention of the Examiner the documents cited on the accompanying Form PTO-1449. No concession is made that these documents are prior art, and applicant expressly reserves the right to antedate the documents as may be appropriate. Applicant requests that each of these documents be made of record in the above-identified application.

Respectfully submitted,



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Form PTO-1449			Docket No.: D-3213		Application No.: 10/550,846		
<b>INFORMATION DISCLOSURE CITATION IN AN APPLICATION</b> <small>(Use several sheets if necessary)</small>			Applicant: Calvez et al.				
			Filing Date: March 24, 2004		Group Art Unit: Unknown		
<b>U. S. PATENT DOCUMENTS</b>							
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE	
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	6,628,695	09/2003	Aldaz et al.				
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						YES	NO
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	WO 99/12235	03/1999	International				
	WO 00/10234	02/2000	International				
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	WO 00/25398	04/2000	International				
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	WO 01/59895	08/2001	International				
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	AA	W.J. Alford et al., "High Power and good beam quality at 980 nm from a vertical external-cavity surface-emitting laser", <i>Journal of the Optical Society of America B (Optical Physics) Opt. Soc. America USA</i> , Vol. 19, No. 4, pages 663-666 (April 2002).					
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	AE	E. Staffan Björlin, "High Gain, High Efficiency Vertical-Cavity Semiconductor Optical Amplifiers", <i>IPRM</i> , 2002, p. 307-310.					
	AF	A. Black, "Wafer Fusion: Materials Issues and Device Results", <i>IEEE Journal Sel. Topics in Quantum Electronics</i> , Vol. 3, No. 3, 1997, p. 943-951.					
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	AH	H. Bourdouce, "Design of Ultra-Fast Dual-Wavelength Resonant-Cavity-Enhanced Schottky Photodetectors", <i>IEEE Journal of Quantum Electronics</i> , Vol. 37, No. 1, 2001, p. 63-68.					
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	AL	R.P. Espindola et al., "Penalty-free 10 Gbit/s single-channel co-pumped distributed Raman amplification using low RIN 14xx nm DFB pump", <i>Electron. Letts.</i> , 38, 3, 2002, p. 113.					
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	AN	M.F. Ferreira et al., "Impact of Stimulated Brillouin Scattering on Fibre Raman Amplifiers", <i>Electronics Letters</i> , Vol. 27, No. 17, 1991, p. 1576-1577.					
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	AX	S. Hoogland et al., "Passively mode-locked diode-pumped Surface-emitting semiconductor laser", <i>IEEE Photonics Tech. Letters</i> , Vol. 12, No. 9, 2000, p. 1135-1137.				
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**OTHER DOCUMENTS** (Including Author, Title, Date, Pertinent Pages, Etc.)

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	BQ	M. Schulze, "Technologischer Durchbruch mit blauen Festkörperlasern", <i>Photonik</i> 3, 2001.				
	BR	C. Stewen et al., "A 1-k W CW Thin Disc Laser", <i>IEEE J. of Sel. Topics Quant. Electron.</i> , Vol. 6, No. 4, 2000, p. 650-657.				
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	BT	E. Yablonovitch et al., "Van der Waals bonding of GaAs epitaxial liftoff films onto arbitrary substrates", <i>Appl. Phys. Lett.</i> , Vol. 56, No. 24, 1990, p. 2419-2421.				
	BU	F. Yang et al., "Edge-emitting quantum well laser with Bragg reflectors", <i>Appl. Phys. Lett.</i> , Vol. 66, No. 22, 1995, p. 2949-2951.				
	BV	Coherent Laser Division. Sapphire Optically Pumped Semiconductor Lasers, Copyright 2002, Coherent, Inc.				
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